

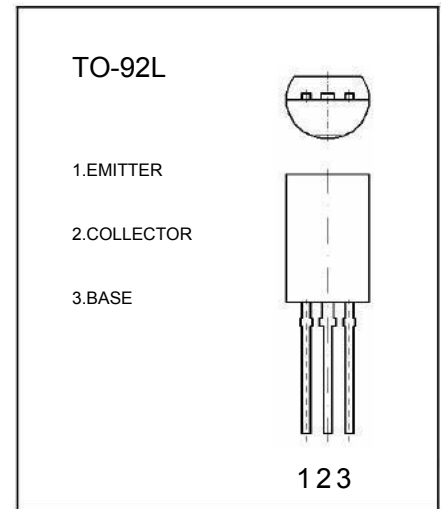


TO-92L Plastic-Encapsulate Transistors

A1222 TRANSISTOR(PNP)

FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with C2959



MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.5	A
P_C	Collector Power Dissipation	1.0	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=-100\text{V}, I_E=0$			-200	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-200	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-100\text{mA}$	100	150	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1\text{A}, I_B=-200\text{mA}$		-0.6	-0.9	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-1\text{A}, I_B=-200\text{mA}$		-1.1	-0.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-20\text{mA}$	30	45		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	100-200	160-320	200-400